SEMICONDUCTOR COMPONENT WITH INCREASED DIELECTRIC STRENGTH AND/OR REDUCED ON RESISTANCE

Abstract

The invention relates to a semiconductor component having a first semiconductor zone of a first conduction type, a second semiconductor zone of a second conduction type and a drift zone arranged between the first and second semiconductor zones, which drift zone has at least two semiconductor zones doped complementarily to one another, the degree of compensation varying at least in a section of the drift zone in a direction perpendicular to a current flow direction running between the first and second semiconductor zones.